



ACE14935M

Dual P-Channel 30-V (D-S) MOSFET

Description

These miniature surface mount MOSFETs utilize High Cell Density process. Low $R_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

Features

- Low $R_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SOP-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Extended VGS range (± 25) for battery pack applications

Product Summary		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
-30	0.021 @ $V_{GS} = -10V$	-7.8
	0.035 @ $V_{GS} = -4.5V$	-6.0

Absolute Maximum Ratings

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 25	V
Continuous Drain Current ^a	I_D	$T_A=25^\circ C$	-7.8
		$T_A=70^\circ C$	-6.2
Pulsed Drain Current ^b	I_{DM}	± 30	A
Continuous Source Current (Diode Conduction) ^a	I_S	-1.7	A
Power Dissipation ^a	P_D	$T_A=25^\circ C$	2.0
		$T_A=70^\circ C$	1.3
Operating temperature / storage temperature	T_J/T_{STG}	-55~150	$^\circ C$

Thermal Resistance Ratings			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	t <= 10 sec	62.5
		Steady State	110

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

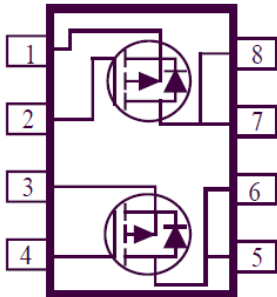


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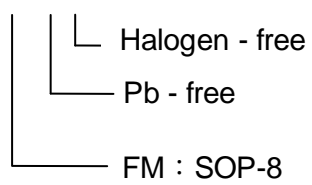
Packaging Type

SOP-8



Ordering information

ACE14935M XX + H





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Electrical Characteristics

$T_A=25^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-1		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 25 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
		$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-40			A
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = -10 \text{ V}, I_D = -7.8 \text{ A}$		19	21	m Ω
		$V_{GS} = -4.5 \text{ V}, I_D = -6.0 \text{ A}$		28	35	
Forward Transconductance	g_{fs}	$V_{DS} = -10 \text{ V}, I_D = -7.8 \text{ A}$		22		S
Diode Forward Voltage	V_{SD}	$I_S = 1.7 \text{ A}, V_{GS} = 0 \text{ V}$		-0.7	-1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V}, I_D = -7.8 \text{ A}$		15		nC
Gate-Source Charge	Q_{gs}			5.2		
Gate-Drain Charge	Q_{gd}			5.8		
Turn-On Delay Time	$t_d(on)$	$V_{DD} = -15 \text{ V}, R_L = 6 \Omega, I_D = -1 \text{ A},$ $V_{GEN} = -10 \text{ V}$		15		ns
Rise Time	t_r			12		
Turn-Off Delay Time	$t_d(off)$			62		
Fall Time	t_f			46		

Note :

- a. Pulse test: $PW \leq 300 \mu\text{s}$ duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing



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Typical Performance Characteristics

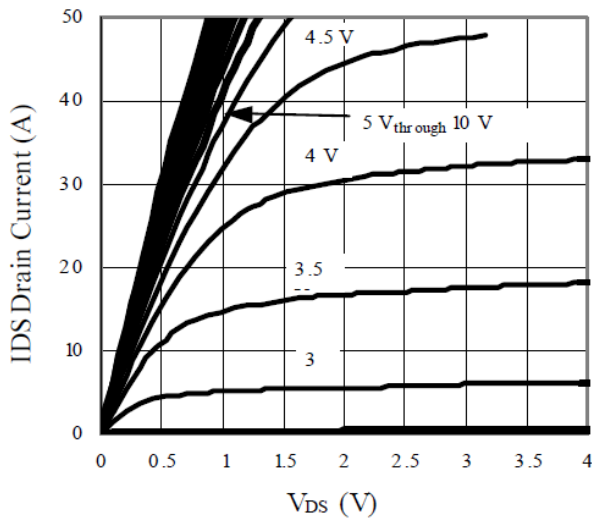


Figure 1. Output Characteristics

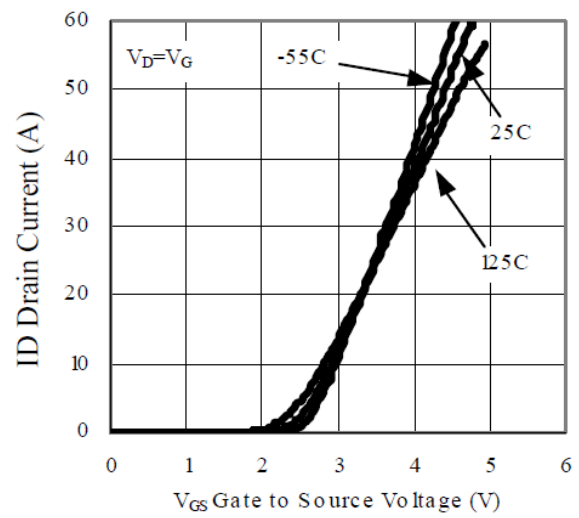


Figure 2. Transfer Characteristics

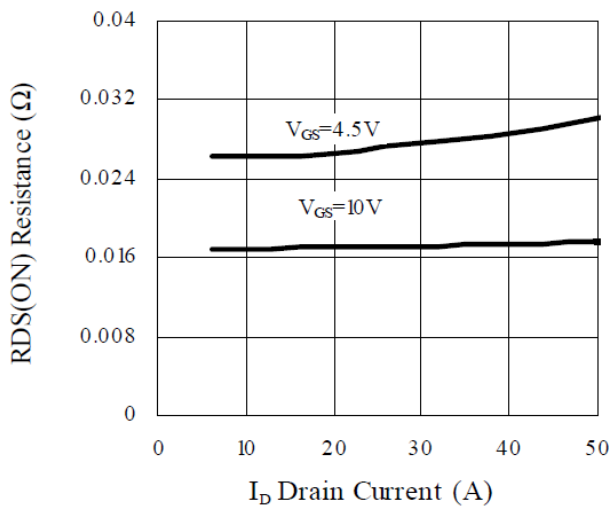


Figure 3. On-Resistance vs. Drain Current

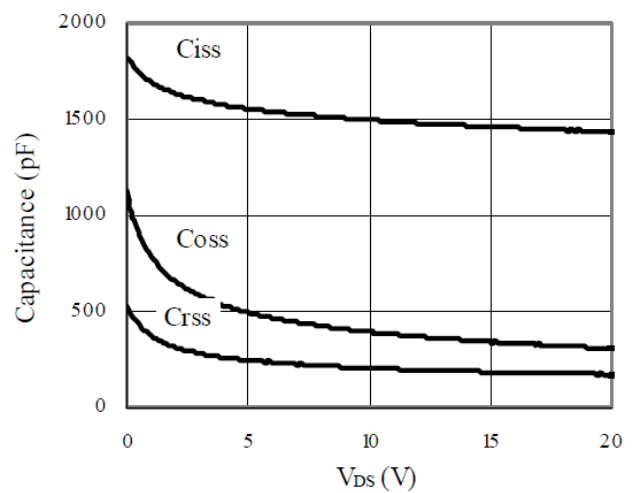


Figure 4. Capacitance

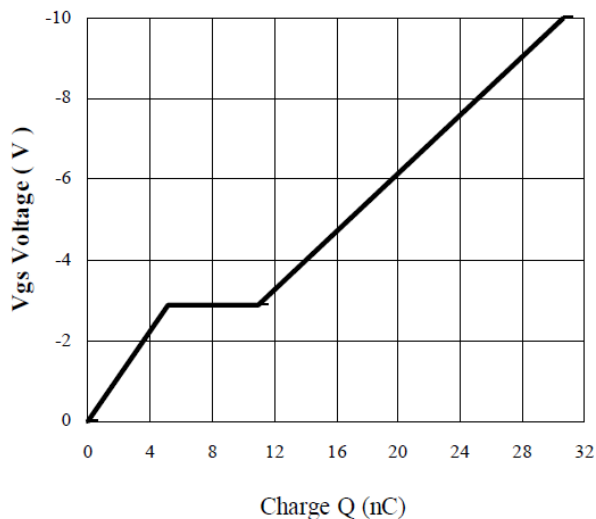


Figure 5. Gate Charge

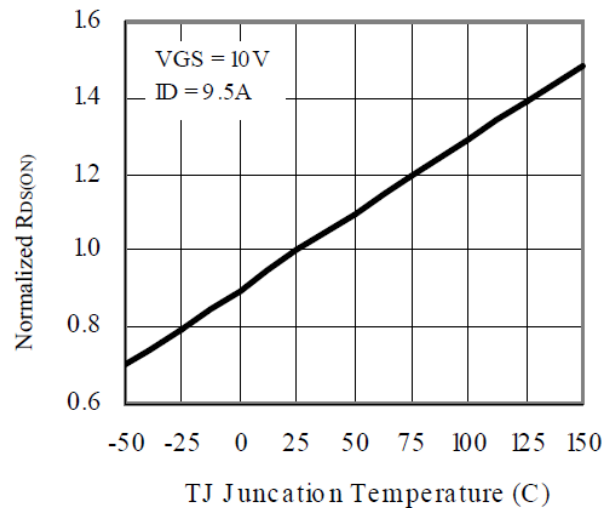


Figure 6. On-Resistance vs. Junction Temperature



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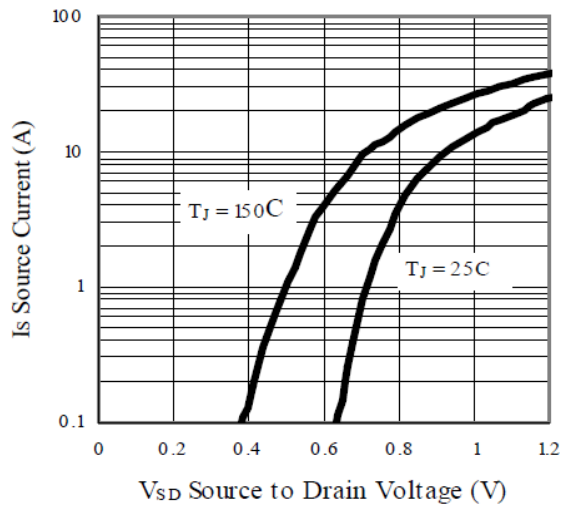


Figure 7. Source-Drain Diode Forward Voltage

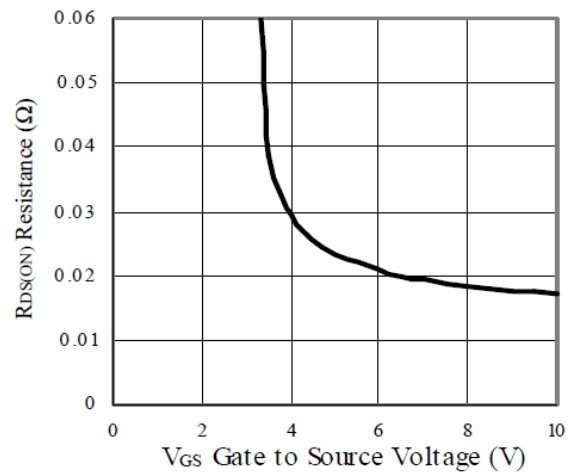


Figure 8. On-Resistance vs. Gate-to-Source Voltage

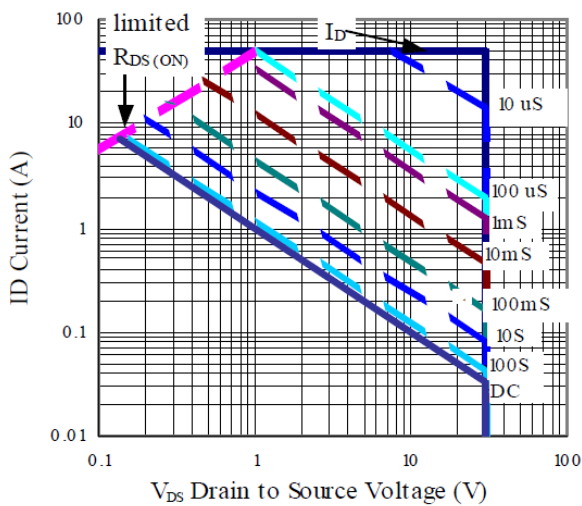


Figure 9. Maximum Safe Operating Area

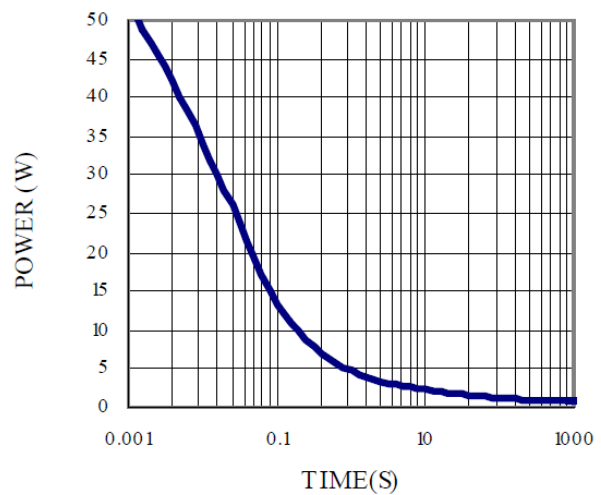


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

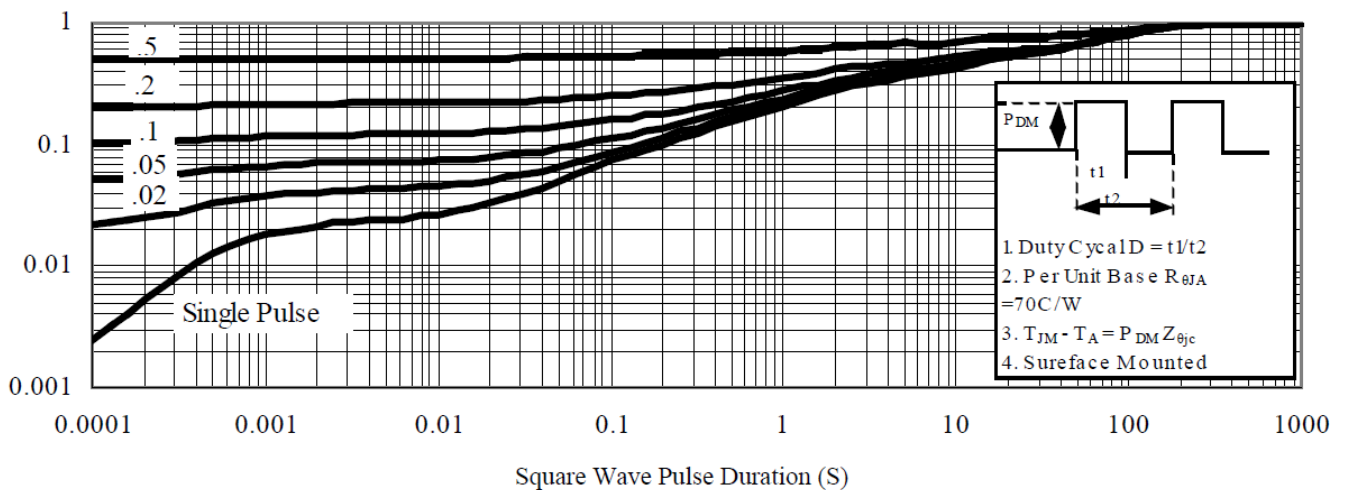


Figure 11. Transient Thermal Response Curve

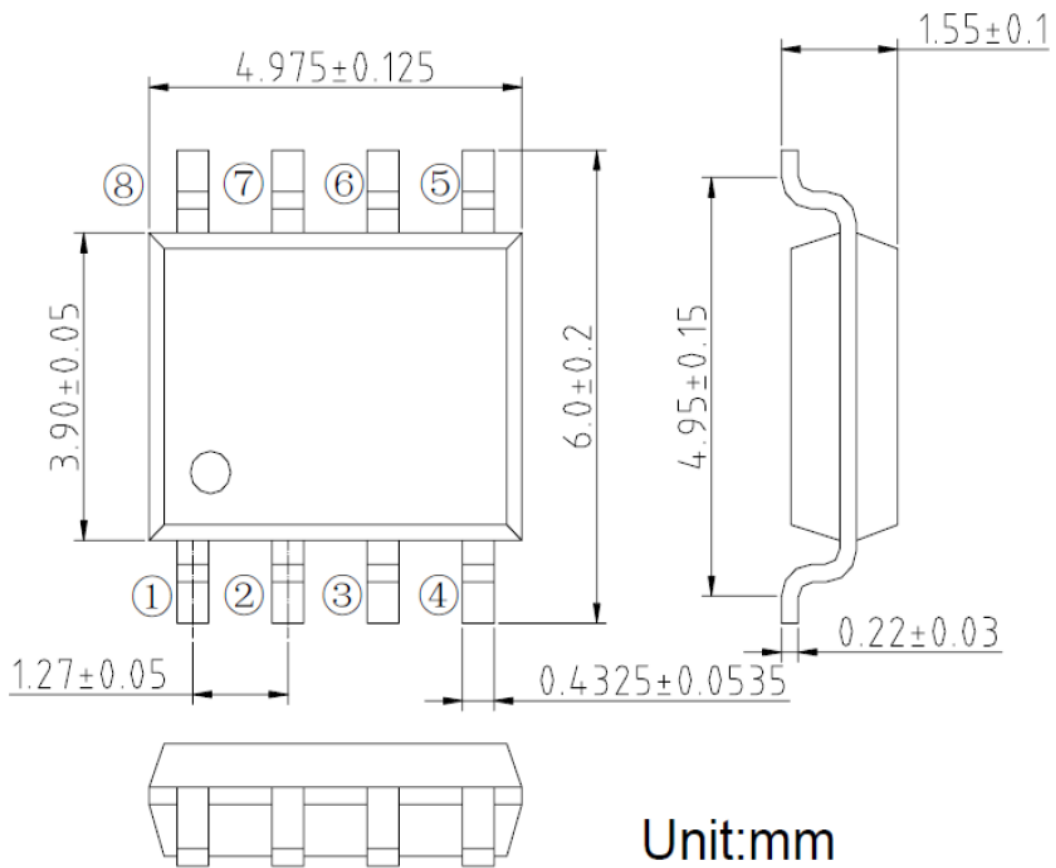


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Packing Information

SOP-8





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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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